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**(54) MANUFACTURE OF
SEMICONDUCTOR DEVICE**

(57) Abstract:

PURPOSE: To provide a forming method of a silicon nitride film wherein the improvement of oxidation resistance and high speed of film formation are compatible with each other.

CONSTITUTION: A silicon nitride film is formed by a thermal CVD method using silane and ammonia as material gas, at a temperature lower

than or equal to 630°C and a pressure higher than or equal to 10Torr. In this case, higher order silane such as disilane and trisilane may be used instead of silane as the material gas, and hydrazine or derivative of hydrazine such as monomethylhydrazine and trimethylhydrazine may be used instead of ammonia as the material gas.

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